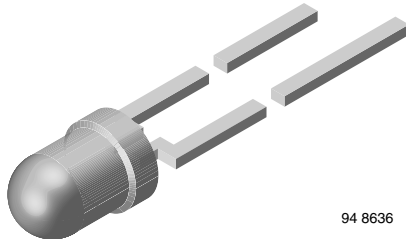


## High Speed Infrared Emitting Diode, 940 nm, GaAlAs, MQW



94 8636

### DESCRIPTION

VSLB3940 is a high speed infrared emitting diode in GaAlAs, MQW technology, molded in a clear plastic package.

### FEATURES

- Package type: leaded
- Package form: T-1, clear epoxy
- Dimensions: Ø 3 mm
- Peak wavelength:  $\lambda_p = 940$  nm
- High speed
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 22^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching to Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Infrared remote control units
- Free air transmission systems
- Infrared source for optical counters and card readers

### PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\varphi$ (deg) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|-----------------|------------------|------------|
| VSLB3940  | 65            | $\pm 22$        | 940              | 15         |

#### Note

Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| VSLB3940      | Bulk      | MOQ: 5000 pcs, 5000 pcs/bulk | T-1          |

#### Note

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

| PARAMETER                           | TEST CONDITION                         | SYMBOL     | VALUE         | UNIT       |
|-------------------------------------|--|------------|---------------|------------|
| Reverse voltage                     |  | $V_R$      | 5             | V          |
| Forward current                     |  | $I_F$      | 100           | mA         |
| Peak forward current                | $t_p/T = 0.1, t_p = 100 \mu s$         | $I_{FM}$   | 1             | A          |
| Surge forward current               | $t_p = 100 \mu s$                      | $I_{FSM}$  | 1.5           | A          |
| Power dissipation                   |  | $P_V$      | 160           | mW         |
| Junction temperature                |  | $T_j$      | 100           | $^\circ C$ |
| Operating temperature range         |  | $T_{amb}$  | - 40 to + 85  | $^\circ C$ |
| Storage temperature range           |  | $T_{stg}$  | - 40 to + 100 | $^\circ C$ |
| Soldering temperature               | $t \leq 5$ s, 2 mm from case           | $T_{sd}$   | 260           | $^\circ C$ |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm, soldered on PCB | $R_{thJA}$ | 300           | K/W        |

#### Note

$T_{amb} = 25 \text{ }^\circ C$ , unless otherwise specified

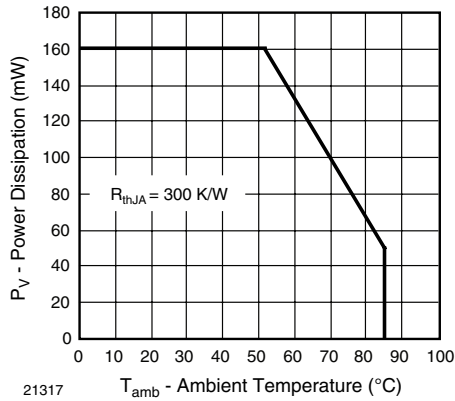


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

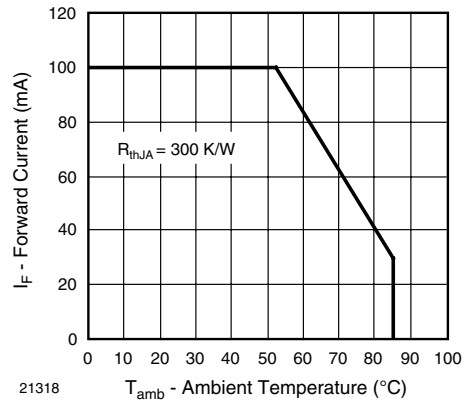


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS                     |  |                             |      |        |      |       |
|---|--|-----------------------------|------|--------|------|-------|
| PARAMETER                                 | TEST CONDITION   | SYMBOL                      | MIN. | TYP.   | MAX. | UNIT  |
| Forward voltage                           | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | V <sub>F</sub>              | 1.15 | 1.35   | 1.6  | V     |
|   | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs                | V <sub>F</sub>              |      | 2.2    |      | V     |
| Temperature coefficient of V <sub>F</sub> | I <sub>F</sub> = 1 mA  | TK <sub>V<sub>F</sub></sub> |      | - 1.5  |      | mV/K  |
|   | I <sub>F</sub> = 100 mA                                      | TK <sub>V<sub>F</sub></sub> |      | - 1.1  |      | mV/K  |
| Reverse current                           | V <sub>R</sub> = 5 V   | I <sub>R</sub>              |      |        | 10   | μA    |
| Junction capacitance                      | V <sub>R</sub> = 0 V, f = 1 MHz,<br>E = 0 mW/cm <sup>2</sup> | C <sub>J</sub>              |      | 70     |      | pF    |
| Radiant intensity                         | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | I <sub>e</sub>              | 32   | 65     | 110  | mW/sr |
|   | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs                | I <sub>e</sub>              |      | 650    |      | mW/sr |
| Radiant power                             | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | φ <sub>e</sub>              |      | 40     |      | mW    |
| Temperature coefficient of radiant power  | I <sub>F</sub> = 1 mA  | TK <sub>φ<sub>e</sub></sub> |      | - 1.1  |      | %/K   |
|   | I <sub>F</sub> = 100 mA                                      | TK <sub>φ<sub>e</sub></sub> |      | - 0.51 |      | %/K   |
| Angle of half intensity                   |  | φ                           |      | ± 22   |      | deg   |
| Peak wavelength                           | I <sub>F</sub> = 30 mA                                       | λ <sub>p</sub>              |      | 940    |      | nm    |
| Spectral bandwidth                        | I <sub>F</sub> = 30 mA                                       | Δλ                          |      | 25     |      | nm    |
| Temperature coefficient of λ <sub>p</sub> | I <sub>F</sub> = 30 mA                                       | TK <sub>λ<sub>p</sub></sub> |      | 0.25   |      | nm    |
| Rise time                                 | I <sub>F</sub> = 100 mA, 20 % to 80 %                        | t <sub>r</sub>              |      | 15     |      | ns    |
| Fall time                                 | I <sub>F</sub> = 100 mA, 20 % to 80 %                        | t <sub>f</sub>              |      | 15     |      | ns    |
| Virtual source diameter                   |  | d                           |      | 2      |      | mm    |

**Note**

T<sub>amb</sub> = 25 °C, unless otherwise specified

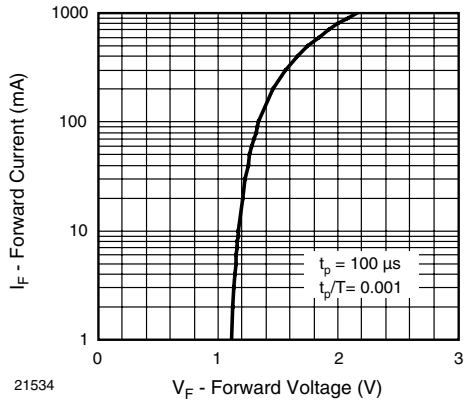
**BASIC CHARACTERISTICS**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified


Fig. 3 - Forward Current vs. Forward Voltage

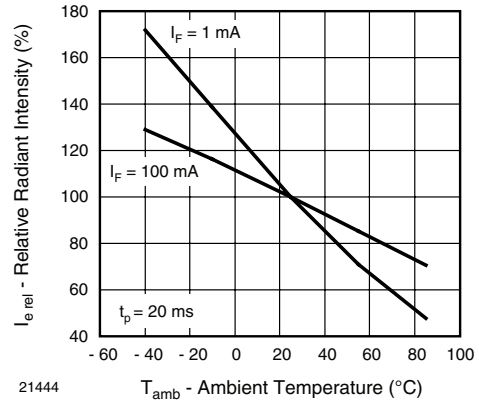


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

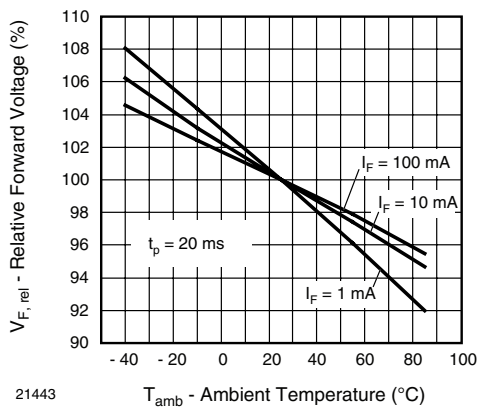


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

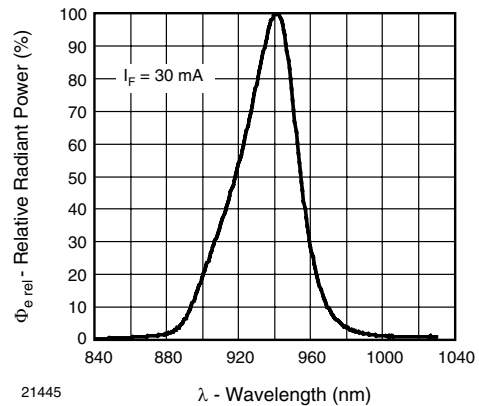


Fig. 7 - Relative Radiant Power vs. Wavelength

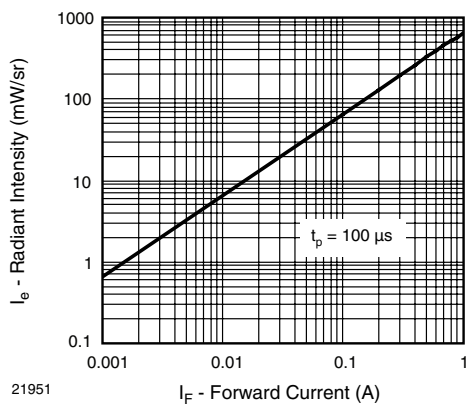


Fig. 5 - Radiant Intensity vs. Forward Current

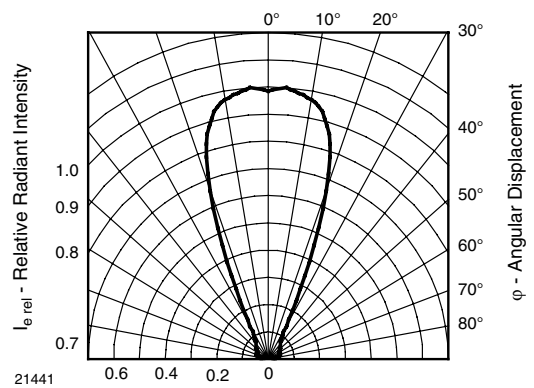
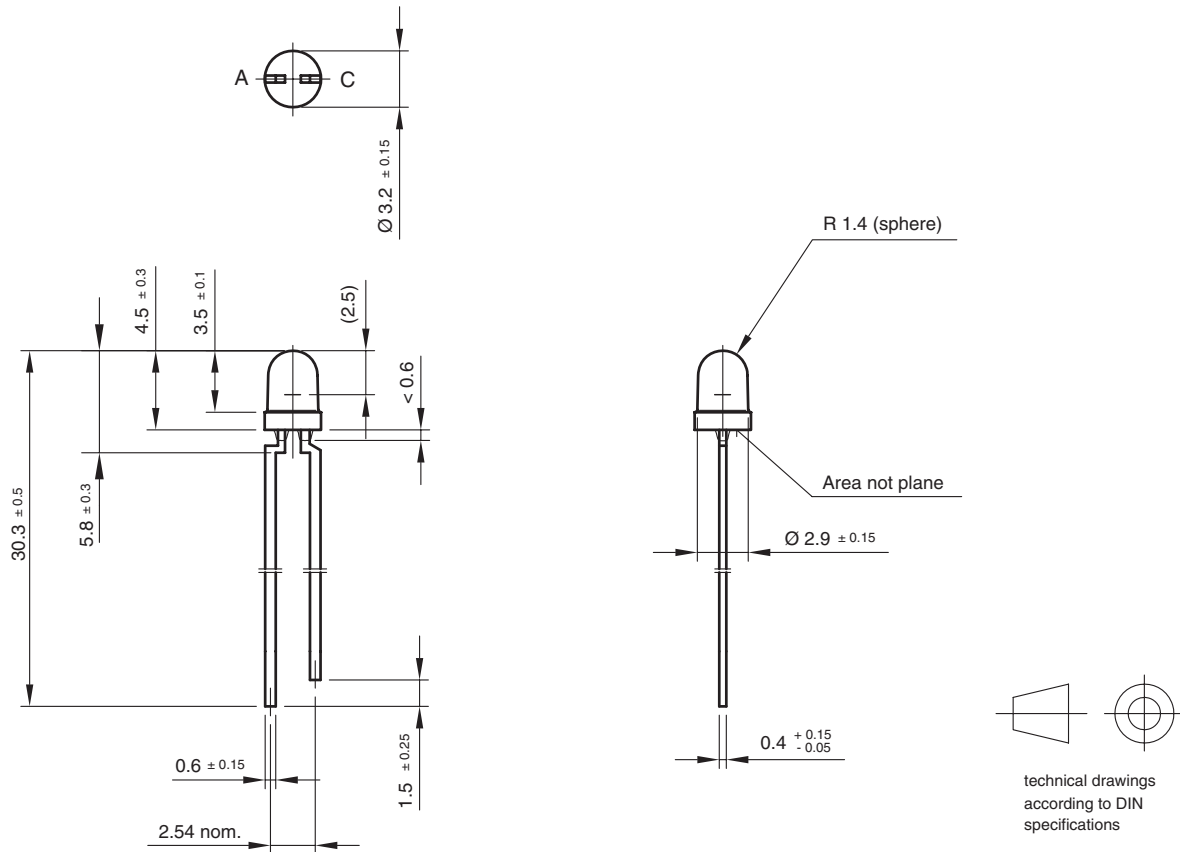


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

**PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.544-5255.01-4  
Issue: 7; 25.09.08  
95 10913



## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.